

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listing, of claims in the application:

### **Listing of Claims:**

1. (Currently Amended) An electrophoretic display, comprising:  
a gate line which extends that runs in a first direction;  
a data line which extends that runs in a second direction substantially perpendicular to the first direction;[[ and]]  
a first pixel electrode formed on an area where overlapping one of the gate line intersects and the data line[[,]]; and  
a second pixel electrode overlapping the one of the gate line and the data line, wherein a portion of the pixel electrode overlaps a portion of the gate line.
2. (Currently Amended) [[An]]The electrophoretic display of claim 1,  
wherein a portion of the first pixel electrode and a portion of the second pixel electrode overlap[[s]] a portion of a width of the data line extending in the second direction between adjacent gatethe data lines.
3. (Currently Amended) [[An]]The electrophoretic display of claim 1, further comprising:  
an insulating layer interposed between the data line and the pixel electrode one of the first pixel electrode and the second pixel electrode,  
wherein the insulating layer has a dielectric constant lower than 4.
4. (Currently Amended) [[An]]The electrophoretic display of claim 1,  
wherein the data line is made of a metal such as selected from a group consisting of Mo, Mo alloy, Cr, Ta and Ti.
5. (Currently amended) [[An]]The electrophoretic display of claim 1, further comprising:  
a thin film transistor having a channel; and comprising:

a channel;

a source electrode; and

a drain electrode;

wherein the first pixel electrode and the second pixel electrode are made of opaque material, and

wherein the first pixel electrode and the second pixel electrode overlap the channel of the thin film transistor.

6. (Currently Amended) The electrophoretic display of claim 3,  
wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

7. (Currently Amended) An electrophoretic display, comprising:

a substrate;

a gate line which extends in a first direction; and

a data line which extends in a second direction substantially perpendicular to the first direction;

a thin film transistor comprising:

a channel;

a gate electrode;

a source electrode;

a drain electrode; and

a semiconductor layer;

an opaque layer formed on the semiconductor layer and disposed over the channel of the thin film transistor;

~~wherein the opaque layer lies opposite to the gate electrode with the semiconductor layer disposed therebetween.~~

a first pixel electrode overlapping one of the gate line and the data line; and

a second pixel electrode overlapping the one of the gate line and the data line.

8. (Currently Amended) The electrophoretic display of claim 7, ~~further comprising:~~  
~~a data line; and~~

~~a gate line;~~

wherein ~~[[the]]~~an inclination angle of the gate line or the data line relative to ~~[[the]]~~a surface of the substrate ranges from between about 20 degrees to about 80 degrees.

9. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 7, further comprising:  
an insulating layer formed between the data line and one of the first pixel electrode and the second pixel electrode,

wherein the insulating layer has a dielectric constant smaller than 4.

10. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 7,  
wherein the data line is made of a metal such as selected from a group consisting of Mo, Mo alloy, Cr, Ta and Ti.

11. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 7, ~~further comprising:~~

~~a thin film transistor with a channel;~~

wherein the first pixel electrode and the second pixel electrode are~~[[is]]~~ made of opaque material, and

wherein the first pixel electrode and the second pixel electrode overlap~~[[s]]~~ the channel of the thin film transistor.

12. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 9,  
wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

13. (Canceled)

14. (Currently Amended) An electrophoretic display, comprising:  
a substrate; and

a thin film transistor ~~[[that]]~~formed on a surface of the substrate, the thin film transistor comprises~~comprising:~~

a source electrode and a drain electrode formed on the substrate;

a semiconductor layer formed on the source and the drain electrode;  
an insulation layer formed on the semiconductor layer; and  
a gate electrode formed on the insulation layer.

15. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 14, further comprising:

a gate line which extends in a first direction;  
a data line which extends in a second direction substantially parallel to the first direction;  
~~[[and]]~~

a first pixel electrode overlapping one of the gate line and the data line; and,  
~~wherein a portion of the pixel electrode overlaps only a portion of the gate line, and~~  
~~wherein a portion of the pixel electrode overlaps only a portion of the data line.~~  
a second pixel electrode overlapping the one of the gate line and the data line.

16. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 15, further comprising:

~~wherein an insulating layer is between formed between the data line and one of the first~~  
~~pixel electrode and the second pixel electrode, [[and]]~~

wherein the insulating layer has a dielectric constant smaller than 4.

17. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 15,  
wherein the data line is made of a metal such as selected from a group consisting of Mo,  
Mo alloy, Cr, Ta and Ti.

18. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 15,  
wherein ~~[[the]]~~an inclination angle of the gate line or the data line relative to the surface  
of the substrate ranges between about 20 degrees to about 80 degrees.

19. (Currently Amended) ~~[[An]]~~The electrophoretic display of claim 16,  
wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

20. (Currently amended) An electrophoretic display, comprising:  
a gate line which extends in a first direction;  
a data line which extends in a second direction substantially perpendicular to the first direction;  
a first pixel electrode overlapping one of the gate line and the data line;  
a second pixel electrode overlapping the one of the gate line and the data line;  
a common electrode; and  
a plurality of micro-capsules,  
wherein each of the microcapsules of the plurality of microcapsules comprises~~includes~~  
electric ink containing a plurality of color pigment particles,  
wherein a color of the plurality of color pigment particles ~~[[are]]~~is at least one of red,  
green, blue, cyan, yellow, ~~magnetamagenta~~, ~~[[blade]]~~black and white, ~~and~~  
~~wherein a portion of the pixel electrode overlaps a portion of the gate line.~~

21. (Currently amended) ~~[[An]]~~The electrophoretic display of claim 20,  
wherein a portion of the first pixel electrode and a portion of the second pixel electrode  
overlap~~[[s]]~~ a portion of a width of the data line extending in the second direction between  
adjacent gate lines.

22. (Currently amended) ~~[[An]]~~The electrophoretic display of claim 20, further  
comprising:  
an insulating layer formed between the data line and the first pixel electrode and the  
second pixel electrode,  
wherein the insulating layer has a dielectric constant ~~smaller~~lower than 4.

23. (New) The electrophoretic display of claim 1,  
wherein a portion of the first pixel electrode and a portion of the second pixel electrode  
overlap a portion of a width of the gate line extending in the first direction between adjacent data  
lines.